查询2N3420供应商



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2N3420

APPLICATIONS:

- Power Supply
- Pulse Amplifier
- High Frequency Power Switching

FEATURES:

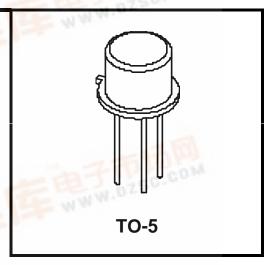
- Meets MIL-S-19500/393
- Collector-Base Voltage: up to 85
- Peak Collector Current: 5A
- High Power Dissipation in TO-5: 15W @ T_C = 100°C
- Fast Switching

3 Amp, 85V, NPN Silicon Power Transistors JAN, JTX, JTXV, JANS

DESCRIPTION:

These power transistors are produced by PPC's DOUBLE DIFFUSED PLANAR process. This technology produces high voltage devices with excellent switching speeds, frequency response, gain linearity, saturation voltages, high current gain, and safe operating areas. They are intended for use in Commercial, Industrial, and Military power switching, amplifier, and regulator applications.

Ultrasonically bonded leads and controlled die mount techniques are utilized to further increase the SOA capability and inherent reliability of these devices. The temperature range to 200°C permits reliable operation in high ambients, and the hermetically sealed package insures maximum reliability and long life.



ABSOLUTE MAXIMUM RATINGS:

SYMBOL	CHARACTERISTIC	VALUE	UNITS
V _{CBO} *	Collector-Base Voltage	85	Volts
$V_{\sf CEO}{}^*$	Collector-Emitter Voltage	60 M W D Z	Volts
$V_{EBO}{}^*$	Emitter-Base Voltage	8	Volts
l _c *	D.C. Collector Current	3	Amps
l _c *	Peak Collector Current	5	Amps
T _{STG} *	Storage Temperature	-65 to 200	∘C
T _J *	Operating Junction Temperature	-65 to 200	∘C
P _T *	Power Dissipation T _C = 25°C Ambient	1.0	Watts
	T _C = 100°C Case	15	Watts

Indicates MIL-S-19500/393



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ELECTRICAL CHARACTERISTICS:

(25°Case Temperature Unless Otherwise Noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VAI	VALUE	
		TEST CONDITIONS	Min.	Max.	Units
BV _{CEO*}	Collector-Emitter Breakdown Voltage	I _C = 50 mAdc, Cond. D (Note 1)	60		Vdc
I _{CEX} *	Collector-Emitter Cutoff Current	V _{EB} = 0.5 Vdc, Cond. A, V _{CE} = 80 Vdc V _{EB} = 0.5 Vdc, Cond. A, T _A = 150°C, V _{CE} = 80 Vdc		0.3 50	μAdc
I _{CEO*}	Collector-Emitter Cutoff Current	V _{CE} = 45 Vdc, Cond. D		5.0	μ Adc μ Adc
I _{EBO} *	Emitter-Base Cutoff Current	V _{EB} = 6 Vdc, Cond. D V _{EB} = 8 Vdc, Cond. D		0.5 10	μ Adc μ Adc
hFE*	D.C. Current Gain (Note 1)	$\begin{split} I_{C} &= 100 \text{ mAdc, } V_{CE} = 2 \text{ Vdc} \\ I_{C} &= 1 \text{ Adc, } V_{CE} = 2 \text{ Vdc} \\ I_{C} &= 2 \text{ Adc, } V_{CE} = 2 \text{ Vdc} \\ I_{C} &= 5 \text{ Adc, } V_{CE} = 5 \text{ Vdc} \\ I_{C} &= 1 \text{ Adc, } V_{CE} = 2 \text{ Vdc, } T_{A} = -55^{\circ}\text{C} \end{split}$	40 40 30 15 10	120 	
V _{CE(sat)} *	Collector-Emitter Saturation Voltage (Note 1)	I _C = 1 Adc, I _B = 0.1 Adc I _C = 2 Adc, I _B = 0.2 Adc		0.25 0.5	Vdc Vdc
V _{BE(sat)*}	Base-Emitter Saturation Voltage (Note 1)	I _C = 1 Adc, I _B = 0.1 Adc I _C = 2 Adc, I _B = 0.2 Adc	0.6 0.7	1.2 1.4	Vdc Vdc
I _{S/b*}	Forward Biased Second Breakdown	$V_{CE} = 5 \text{ Vdc}, T_{C} = 100^{\circ}\text{C}$ $V_{CE} = 37 \text{ Vdc}, T_{C} = 100^{\circ}\text{C}$ $V_{CE} = 60 \text{ Vdc}, T_{C} = 100^{\circ}\text{C}$	3 0.4 185		Adc Adc mAdc
E _{S/b*}	Unclamped Reverse Biased Second Breakdown	I _C = 3 Adc, L = 10 mH, Base Open	45		mj
E _{S/b*}	Clamped Reverse Biased Second Breakdown	I _C = 3 Adc, L = 40 mH, V _{Clamp} = 125V	180		mj
f _T *	Gain Bandwidth Product	I _C = 0.1 Adc, V _{CE} = 10 Vdc, f = 20 MHz	26	160	MHz
C _{Ob} *	Output Capacitance	V _{CB} = 10 Vdc, I _E = 0, f = 1 MHz		150	pf
t _{on}	Turn-on Time	I _C = 1 Adc, I _{B1} = - I _{B2} = 0.1 Adc		0.3	μS
t _{off}	Turn-off Time	$I_C = 1$ Adc, $I_{B1} = -I_{B2} = 0.1$ Adc		1.2	μS

Note 1: Pulse Test: Pulse width = $300\mu Sec.$, duty cycle $\leq 2\%$.

^{*} Indicates MIL-S-19500/393





PACKAGE MECHANICAL DATA:

